### LF2802A



# RF Power MOSFET Transistor 2W, 500-1000MHz, 28V

## M/A-COM Products Released; RoHS Compliant

#### **Features**

- N-Channel enhancement mode device
- DMOS structure
- Lower capacitances for broadband operation
- Common source configuration
- Lower noise floor
- Applications

Broadband linear operation 500 MHz to 1400 MHz

#### **ABSOLUTE MAXIMUM RATINGS AT 25° C**

Parameter	Symbol	Rating	Units
Drain-Source Voltage	$V_{DS}$	65	V
Gate-Source Voltage	$V_{GS}$	20	V
Drain-Source Current	I <sub>DS</sub>	0.7	Α
Power Dissipation	$P_D$	8	W
Junction Temperature	$T_J$	200	°C
Storage Temperature	T <sub>STG</sub>	-55 to +150	°C
Thermal Resistance	$\theta_{\text{JC}}$	21.8	°C/W

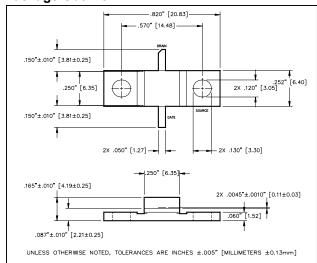
#### TYPICAL DEVICE IMPEDANCE

F (MHz)	Z <sub>IN</sub> (Ω)	Z <sub>LOAD</sub> (Ω)		
500	10.0 - j41.5	40.0 +j53.0		
1000	4.2 - j12.0	11.85 + j33.0		
1400	3.5 - j1.0 7.5 + j23.3			
$V_{DD} = 28V$ , $I_{DQ} = 25mA$ , $P_{OUT} = 2.0 W$				

 $Z_{\text{IN}}$  is the series equivalent input impedance of the device from gate to source.

 $Z_{\text{LOAD}}$  is the optimum series equivalent load impedance as measured from drain to ground.

#### **Package Outline**



LETTER	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	20.70	20.96	.815	.825
В	14.35	14.61	.565	.575
С	13.72	14.22	.540	.560
D	6.27	6.53	.247	.257
E	6.22	6.48	.245	.255
F	6.22	6.48	.245	.255
G	1.14	1.40	.045	.055
Н	2.92	3.18	.115	.125
J	1.40	1.65	.055	.065
К	1.96	2.46	.077	.097
L	3.61	4.37	.142	.172
М	.08	.15	.003	.006

#### **ELECTRICAL CHARACTERISTICS AT 25°C**

Parameter	Symbol	Min	Max	Units	Test Conditions
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	65	-	V	V <sub>GS</sub> = 0.0 V , I <sub>DS</sub> = 1.0 mA
Drain-Source Leakage Current	I <sub>DSS</sub>	-	0.5	mA	V <sub>GS</sub> = 28.0 V , V <sub>GS</sub> = 0.0 V
Gate-Source Leakage Current	I <sub>GSS</sub>	-	0.5	μΑ	V <sub>GS</sub> = 20.0 V , V <sub>DS</sub> = 0.0 V
Gate Threshold Voltage	$V_{GS(TH)}$	2.0	6.0	V	V <sub>DS</sub> = 10.0 V , I <sub>DS</sub> = 5.0 mA
Forward Transconductance	G <sub>M</sub>	40	-	mS	$V_{DS}$ = 28.0 V , $I_{DS}$ = 50.0 mA , $\Delta$ $V_{GS}$ = 1.0V, 80 $\mu$ s Pulse
Input Capacitance	C <sub>ISS</sub>	-	3.5	pF	V <sub>DS</sub> = 28.0 V , F = 1.0 MHz
Output Capacitance	Coss	-	3.75	pF	V <sub>DS</sub> = 28.0 V , F = 1.0 MHz
Reverse Capacitance	C <sub>RSS</sub>	-	1.2	pF	V <sub>DS</sub> = 28.0 V , F = 1.0 MHz
Power Gain	G <sub>P</sub>	10	-	dB	V <sub>DD</sub> = 28.0 V, I <sub>DQ</sub> = 25 mA, P <sub>OUT</sub> = 2.0 W F =1.0 GHz
Drain Efficiency	η <sub>D</sub>	40	-	%	V <sub>DD</sub> = 28.0 V, I <sub>DQ</sub> = 25 mA, P <sub>OUT</sub> = 2.0 W F =1.0 GHz
Load Mismatch Tolerance	VSWR-T	-	20:1	-	V <sub>DD</sub> = 28.0 V, I <sub>DQ</sub> = 25 mA, P <sub>OUT</sub> = 2.0 W F =1.0 GHz

ADVANCED: Data Sheets contain information regarding a product M/A-COM Technology Solutions is considering for development. Performance is based on target specifications, simulated results, and/or prototype measurements. Commitment to develop is not guaranteed.

PRELIMINARY: Data Sheets contain information regarding a product M/A-COM Technology

PRELIMINARY: Data Sheets contain information regarding a product M/A-COM Technology Solutions has under development. Performance is based on engineering tests. Specifications are typical. Mechanical outline has been fixed. Engineering samples and/or test data may be available. Commitment to produce in volume is not guaranteed.

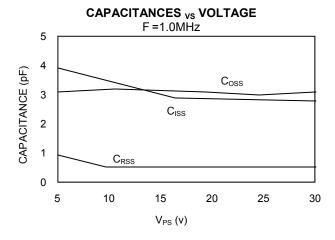
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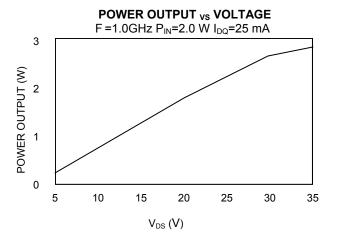


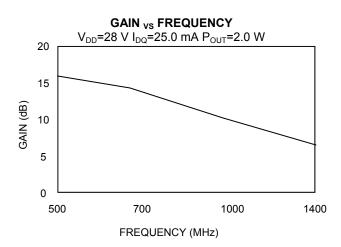
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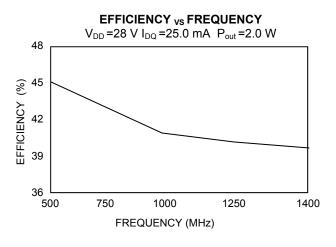
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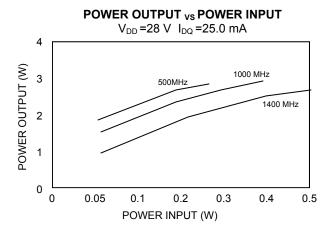
#### **Typical Broadband Performance Curves**











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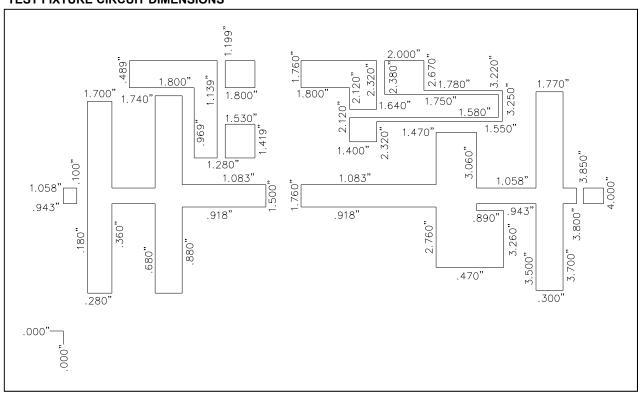
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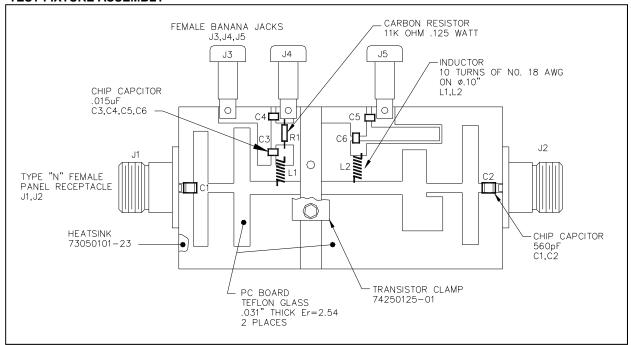
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#### **TEST FIXTURE CIRCUIT DIMENSIONS**



#### **TEST FIXTURE ASSEMBLY**



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